N-Channel Enhancement Mode MOSFET TDM31518

DESCRIPTION

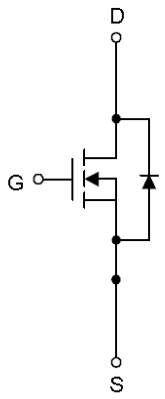
The TDM31518 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

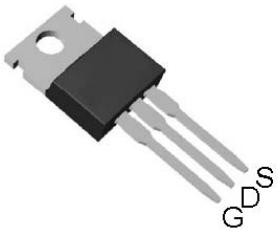
- RDS(ON) < 13.5mΩ @ VGS=10V
- Reliable and Rugged
- Lead free product is available
- TO-220 Package

Application

- PWM applications
- Load switch
- Power management



N-Channel MOSFET



Top View of TO-220

ABSOLUTE MAXIMUM RATINGS(T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	±30	V
Diode Continuous Forward Current	I_S (T_C=25℃)	80	A
Drain Current @ Continuous	I_D (T_C=25℃)	86	A
	I_D (T_C=100℃)	54	A
Drain Current @ Current-Pulsed (Note 1)	I_{DM} (T_C=25℃)	300	A
Maximum Power Dissipation	P_D(T_C=25℃)	250	W
	P_D(T_C=100℃)	100	W
Drain Current @ Continuous	I_D (T_A=25℃)	8	A
	I_D (T_A=70℃)	6	A
Maximum Power Dissipation (T_A=25℃)	P_D (T_A=25℃)	2	W
	P_D (T_A=70℃)	1.25	W
Avalanche Energy, Single pulse(L=0.5mH)	E_{AS}	240	mJ

THERMAL CHARACTERISTICS

Thermal Resistance-Junction to Case	$R_{\theta JC}$（Steady State）	0.5	℃/W
Thermal Resistance,Junction-to-Ambient	$R_{\theta JA}$（Steady State）	62.5	℃/W
Maximum Operating Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{STG}	-55 To 150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃unless otherwise noted)

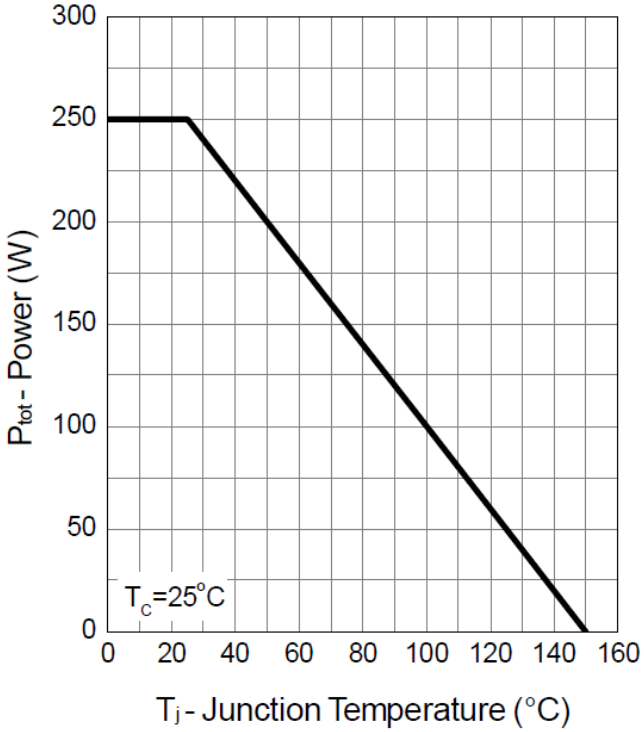
Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	150	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=120V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±30V,V_{DS}=0V	-	-	±100	nA
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS,I_D=250μA	3	4	5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=40A	-	11	13.5	mΩ
DYNAMIC CHARACTERISTICS (Note3)						
Gate Resistance	R_G	V_{DS}=0V,V_{GS}=0V, F=1.0MHz	-	1.0	-	Ω
Input Capacitance	C_{iss}	V_{DS}=30V,V_{GS}=0V, F=1.0MHz	-	5150	6700	PF
Output Capacitance	C_{oss}		-	520	-	PF
Reverse Transfer Capacitance	C_{rss}		-	90	-	PF
SWITCHING CHARACTERISTICS (Note 3)						
Turn-on Delay Time	$t_{d(on)}$	V_{DS}=30V, R_L=30Ω, V_{GEN}=10V,R_G=6Ω	-	32	58	nS
Turn-on Rise Time	t_r	I_D=1A	-	11	20	nS
Turn-Off Delay Time	$t_{d(off)}$		-	68	123	nS
Turn-Off Fall Time	t_f		-	47	85	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=40A,V_{GS}=10V	-	83	116	nC
Gate-Source Charge	Q_{gs}		-	35	-	nC
Gate-Drain Charge	Q_{gd}		-	18	-	nC
Body Diode Reverse Recovery Time	T_{rr}	I_F=40A, dI/dt=100A/μs	-	75	-	nS
Body Diode Reverse Recovery Charge	Q_{rr}		-	240	-	nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 2)	V_{SD}	V_{GS}=0V,I_S=20A	-	0.8	1.3	V

NOTES:

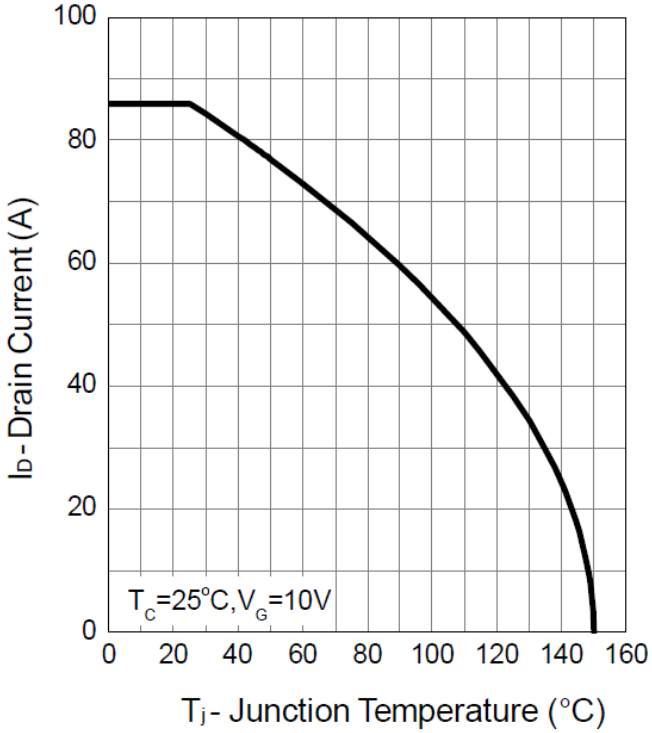
1. Pulse width limited by max. junction temperature.
2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
3. Guaranteed by design, not subject to production testing

Typical Operating Characteristics

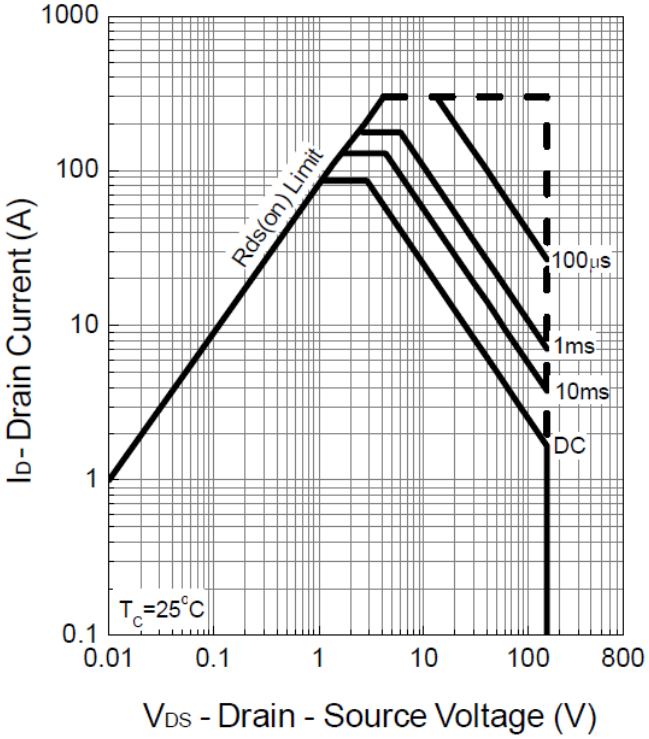
Power Dissipation



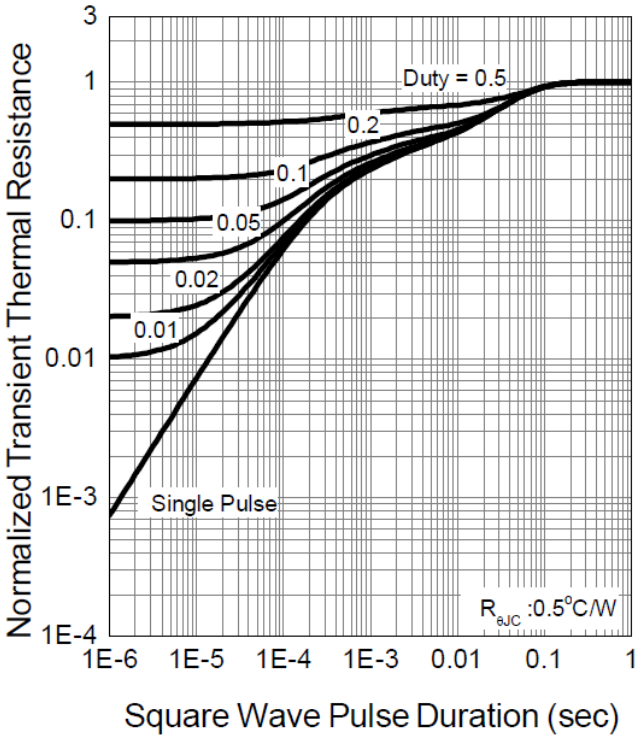
Drain Current



Safe Operation Area

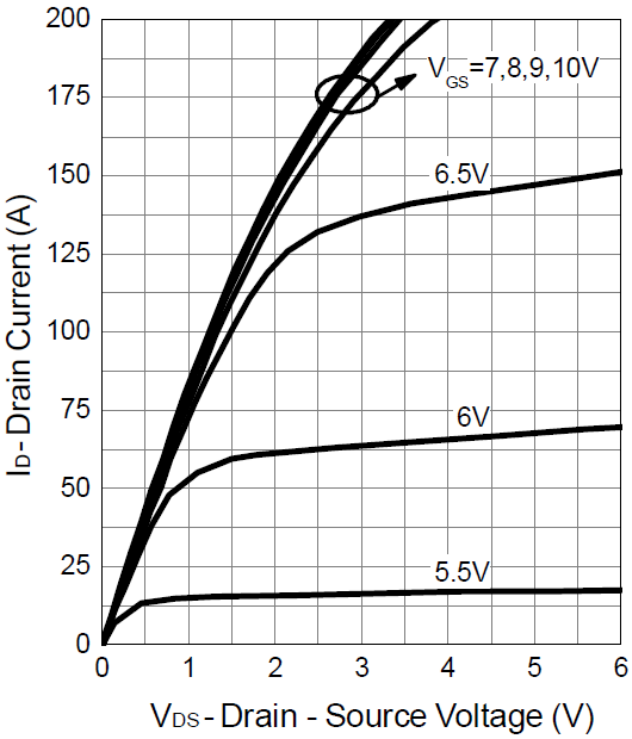


Thermal Transient Impedance

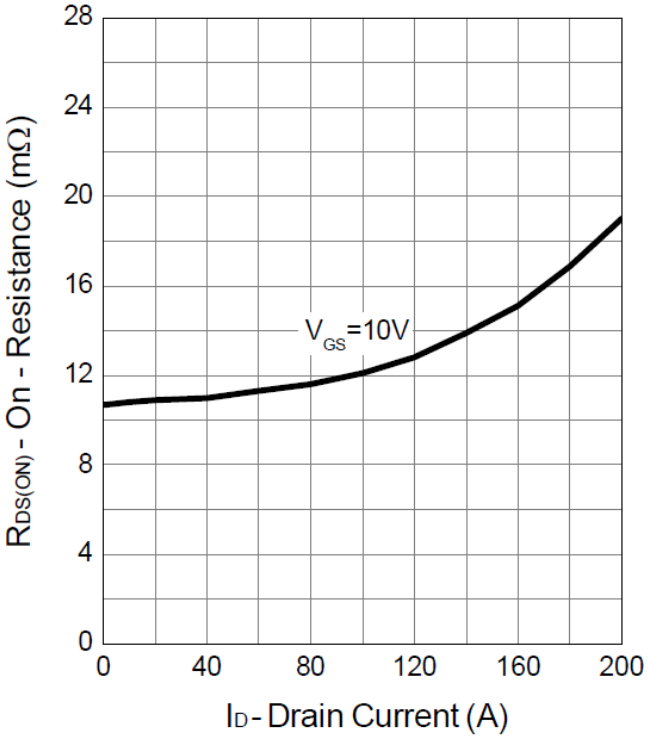


Typical Operating Characteristics (Cont.)

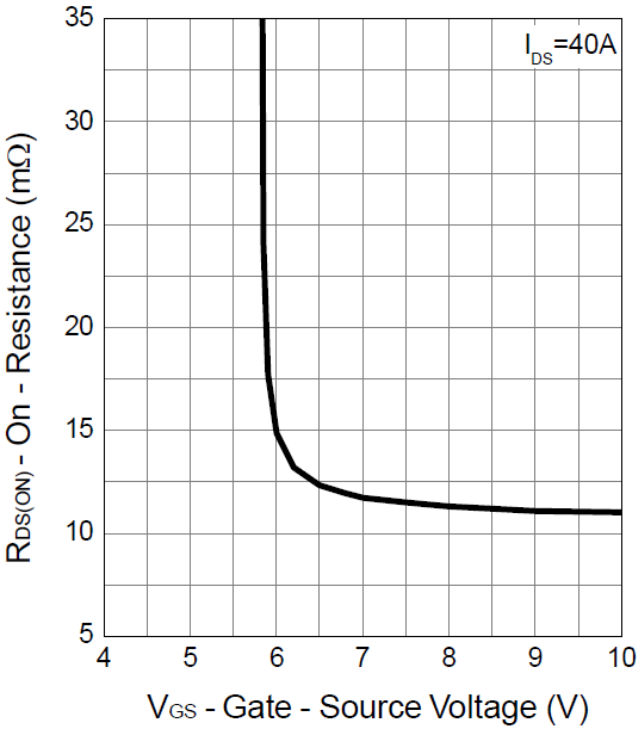
Output Characteristics



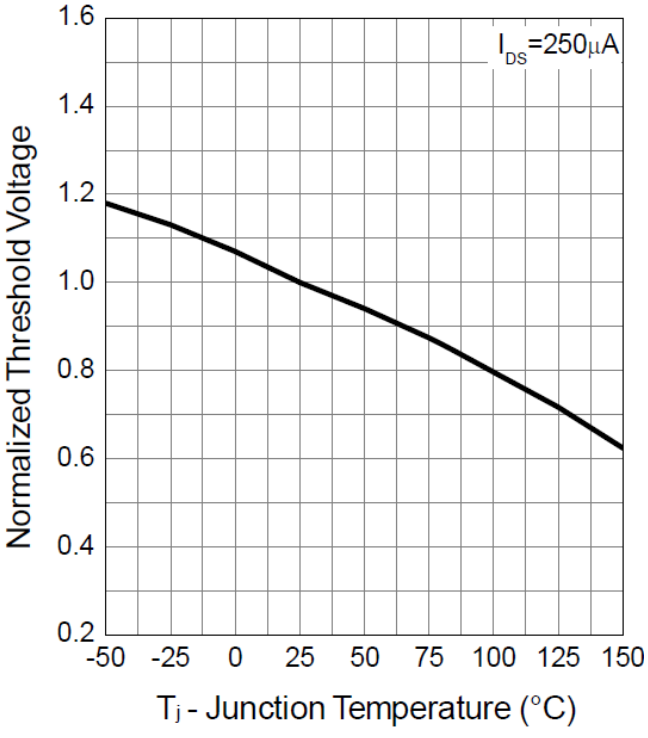
Drain-Source On Resistance



Gate-Source On Resistance

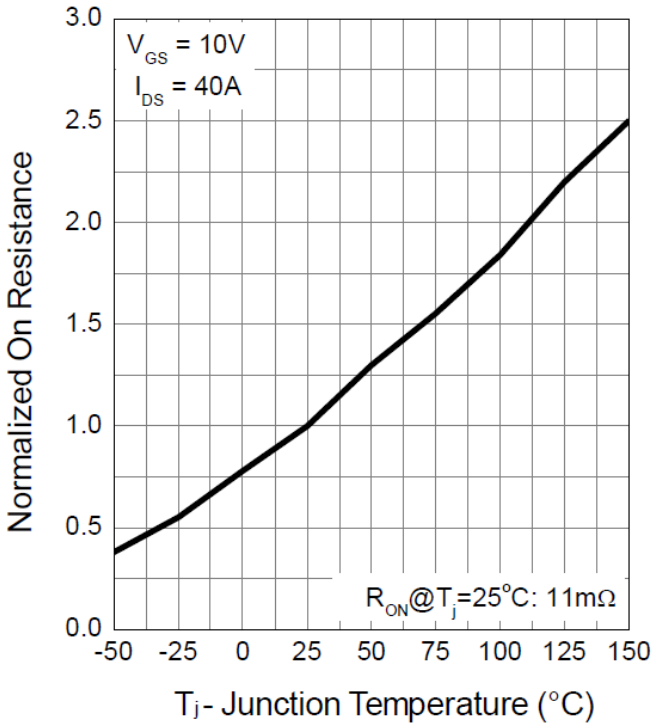


Gate Threshold Voltage

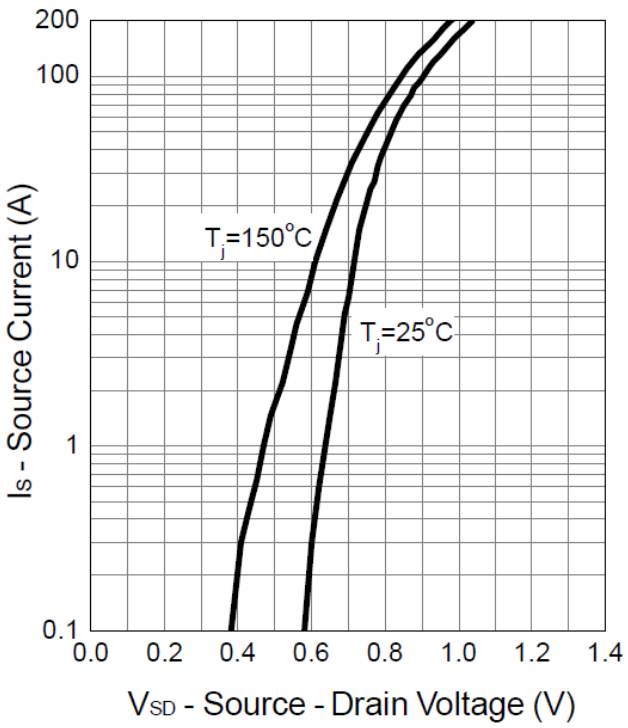


Typical Operating Characteristics (Cont.)

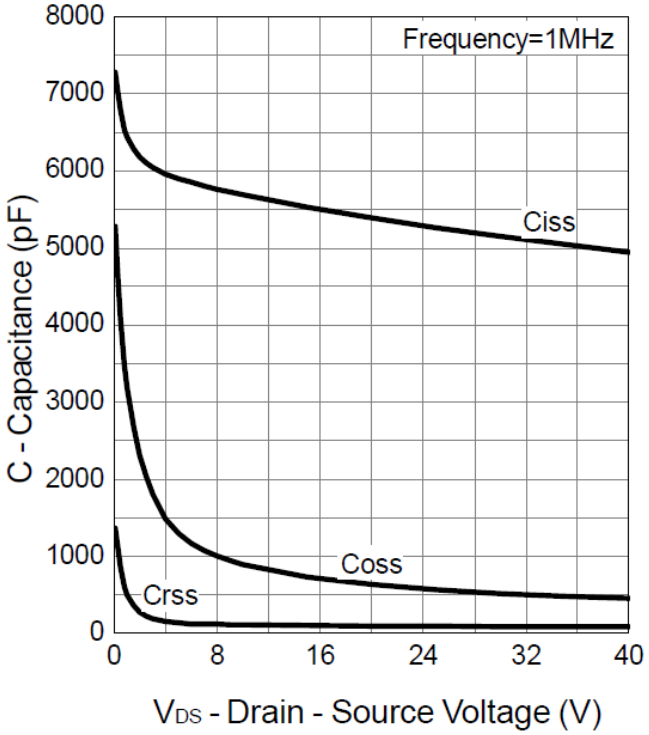
Drain-Source On Resistance



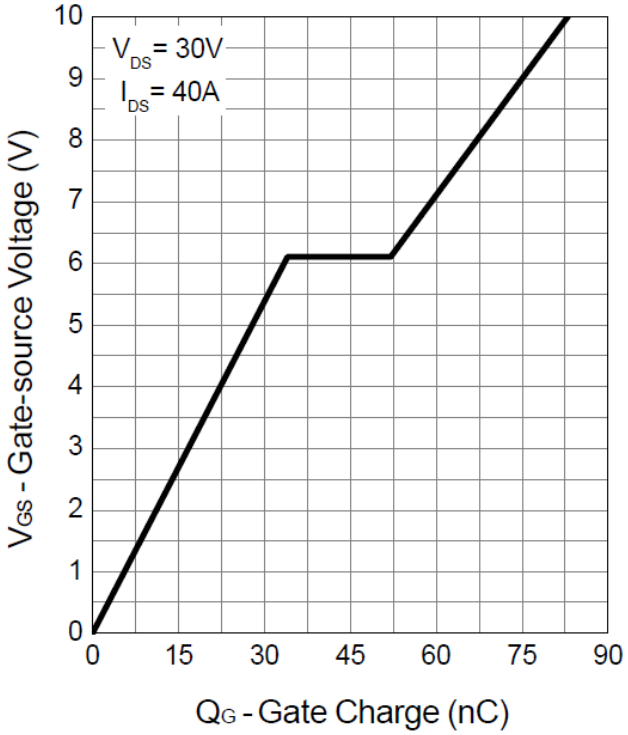
Source-Drain Diode Forward



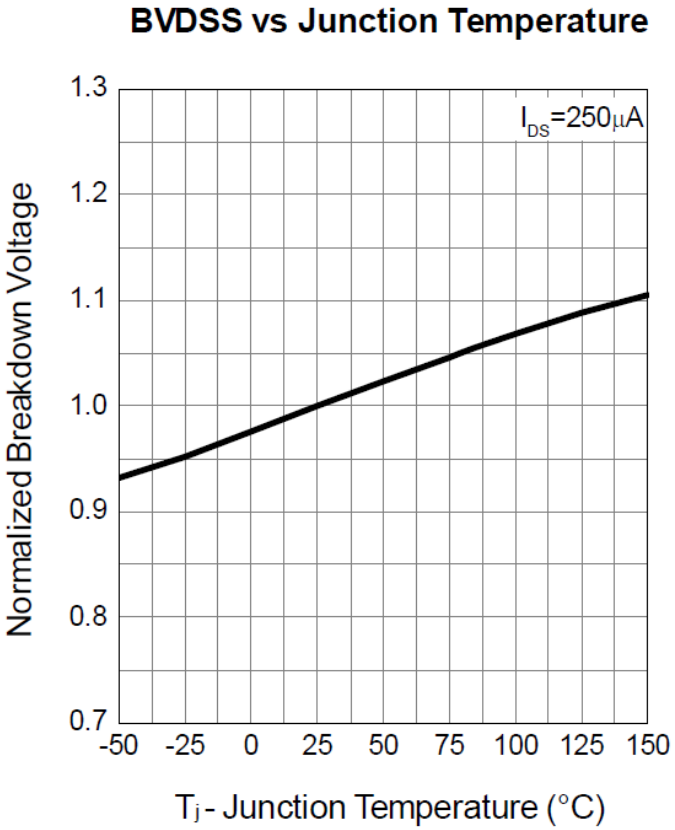
Capacitance



Gate Charge

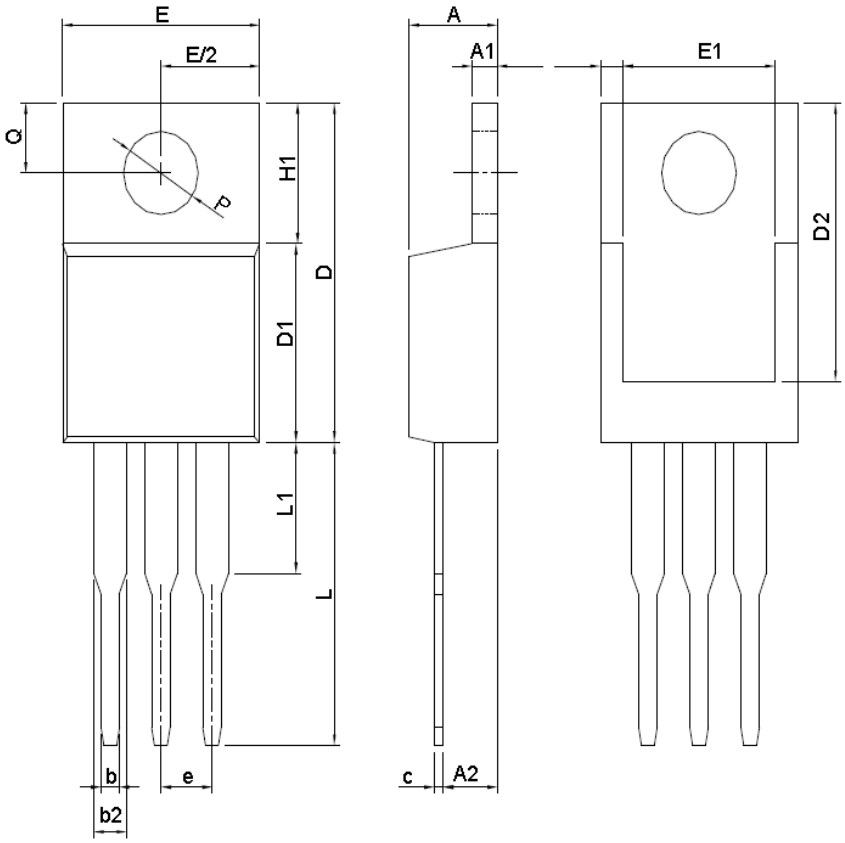


Typical Operating Characteristics (Cont.)



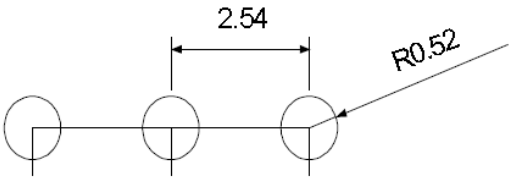
Package Information

TO220 Package



SYMBOL	TO-220			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	3.56	4.83	0.140	0.190
A1	0.51	1.40	0.020	0.055
A2	2.03	2.92	0.080	0.115
b	0.38	1.02	0.015	0.040
b2	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.22	16.51	0.560	0.650
D1	8.38	9.30	0.330	0.366
D2	12.19	13.65	0.480	0.537
E	9.65	10.67	0.380	0.420
E1	6.86	8.89	0.270	0.350
e	2.54 BSC		0.100 BSC	
H1	5.84	6.86	0.230	0.270
L	12.70	14.73	0.500	0.580
L1	-	6.35	-	0.250
P	3.53	4.09	0.139	0.161
Q	2.54	3.43	0.100	0.135

RECOMMENDED LAND PATTERN



UNIT: mm

Design Notes